

Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

<u>Vishay Semiconductor/Diodes Division</u> <u>VS-10CWH02FNTR-M3</u>

For any questions, you can email us directly: sales@integrated-circuit.com



Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



VS-10CWH02FN-M3

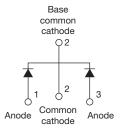
Vishay Semiconductors

Hyperfast Rectifier, 2 x 5 A FRED Pt®



www.vishay.com

TO-252AA (D-PAK)



PRODUCT SUMMARY								
Package	TO-252AA (D-PAK)							
I _{F(AV)}	2 x 5 A							
V_{R}	200 V							
V _F at I _F	0.74 V							
t _{rr} (typ.)	23 ns							
T _J max.	175 °C							
Diode variation	Common cathode							

FEATURES

- · Hyperfast recovery time
- 175 °C max. operating junction temperature
- · Output rectification freewheeling
- Low forward voltage drop reduced Q_{rr} and soft recovery
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



ROHS COMPLIANT HALOGEN FREE

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

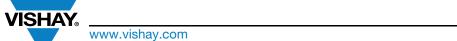
ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V_{RRM}		200	V	
Average rectified forward current	I _{F(AV)}	T _C = 160 °C	10	^	
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	80	Α	
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	200	-	-					
		I _F = 5 A	-	0.90	0.98					
Forward voltage	V _F	I _F = 10 A	-	0.98	1.15	V				
		I _F = 5 A, T _J = 150 °C	-	0.74	0.84).84				
		I _F = 10 A, T _J = 150 °C	-	0.84	1.05					
	I _R	$V_R = V_R$ rated	-	-	4					
Reverse leakage current per leg		T _J = 125 °C, V _R = V _R rated	-	-	40	μA				
		$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$		-	80					
Junction capacitance per leg	C _T	V _R = 600 V	-	17	-	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH				

Revision: 07-Jul-15 **1** Document Number: 93263

Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite Datasheet of VS-10CWH02FNTR-M3 - DIODE ARRAY GP 200V 10A TO252AA

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



VS-10CWH02FN-M3

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time	t _{rr}	$I_F = 1 A, dI_F/dt = 10$	-	23	27				
		T _J = 25 °C		-	21	-	ns - A		
		T _J = 125 °C	$I_F = 5 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 160 \text{ V}$	-	26	-			
Dools recovery as week	I _{RRM}	T _J = 25 °C		-	2	-			
Peak recovery current		T _J = 125 °C		-	3.1	-			
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	20	-	200		
		T _J = 125 °C		-	41	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C				
Thermal resistance, per leg			-	2.7	3.2	°C/W				
junction to case per device	R _{thJC}		-	1.35	1.6	*C/VV				
Annuavimata walaht				0.3		g				
Approximate weight				0.01		OZ.				
Marking device		Case style TO-252AA (D-PAK)	10CWH02FN							

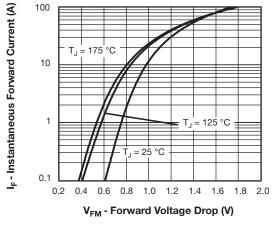


Fig. 1 - Typical Forward Voltage Drop Characteristics

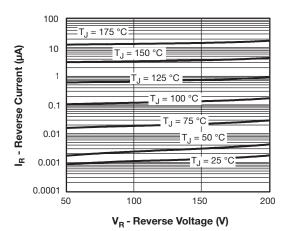


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



www.vishay.com

VS-10CWH02FN-M3

Vishay Semiconductors

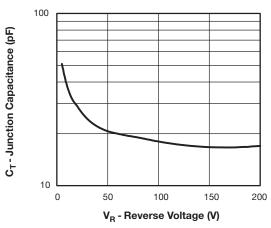


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

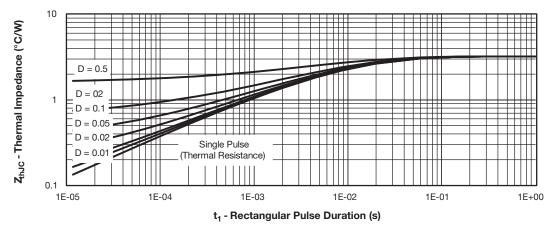


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

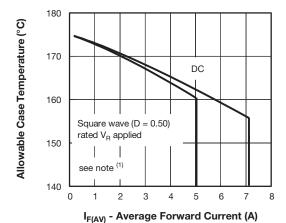


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

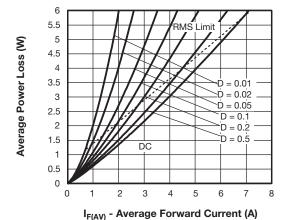


Fig. 6 - Forward Power Loss Characteristics

Note

Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = Inverse power loss = $V_{R1} \times I_{R1} \times I_{R1} \times I_{R2} \times I_{R3} \times I_{R4} \times I_{R4}$

Revision: 07-Jul-15 3 Document Number: 93263 **VISHAY**

Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite

Datasheet of VS-10CWH02FNTR-M3 - DIODE ARRAY GP 200V 10A TO252AA Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

VS-10CWH02FN-M3

www.vishay.com

Vishay Semiconductors

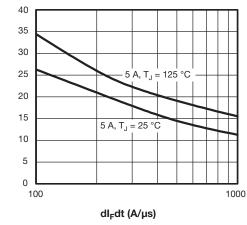


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

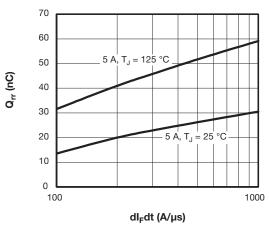


Fig. 8 - Typical Stored Charge vs. dl_F/dt

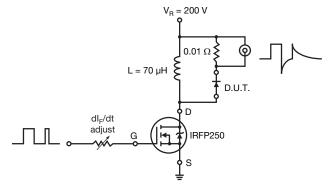
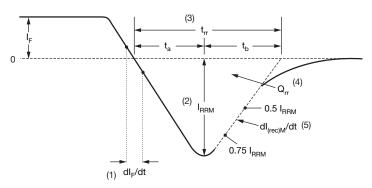


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite

Datasheet of VS-10CWH02FNTR-M3 - DIODE ARRAY GP 200V 10A TO252AA Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

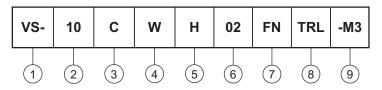


VS-10CWH02FN-M3

Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (10 = 10 A)

- Circuit configuration:

C = common cathode

4 - Package identifier:

W = D-PAK

5 - H = hyperfast recovery

Voltage rating (02 = 200 V)

7 - FN = TO-252AA

6

8 - • None = tube

• TR = tape and reel

• TRL = tape and reel (left oriented)

• TRR = tape and reel (right oriented)

9 - Environmental digit:

-M3 = halogen-free, RoHS-compliant and terminations lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-10CWH02FN-M3	75	3000	Antistatic plastic tube						
VS-10CWH02FNTR-M3	2000	2000	13" diameter reel						
VS-10CWH02FNTRL-M3	3000	3000	13" diameter reel						
VS-10CWH02FNTRR-M3	3000	3000	13" diameter reel						

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95016						
Part marking information	www.vishay.com/doc?95176						
Packaging information	www.vishay.com/doc?95033						
SPICE model	www.vishay.com/doc?95376						

Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite

Datasheet of VS-10CWH02FNTR-M3 - DIODE ARRAY GP 200V 10A TO252AA Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

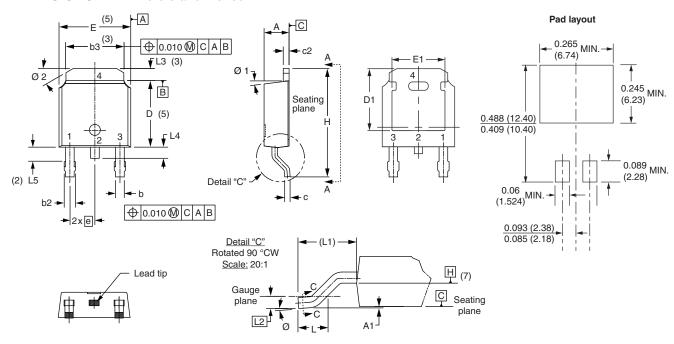


Outline Dimensions

Vishay Semiconductors

D-PAK (TO-252AA)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	MILLIMETERS		INCHES		NOTES	NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES	
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES		
Α	2.18	2.39	0.086	0.094			е	2.29 BSC		0.090 BSC				
A1	-	0.13	-	0.005			Н	9.40	10.41	0.370	0.410			
b	0.64	0.89	0.025	0.035			L	1.40	1.78	0.055	0.070			
b2	0.76	1.14	0.030	0.045			L1	2.74	2.74 BSC 0.10		REF.			
b3	4.95	5.46	0.195	0.215	3		L2	0.51	BSC	SC 0.020		0.020 BSC		
С	0.46	0.61	0.018	0.024			L3	0.89	1.27	0.035	0.050	3		
c2	0.46	0.89	0.018	0.035			L4		1.02		0.040			
D	5.97	6.22	0.235	0.245	5		L5	1.14	1.52	0.045	0.060	2		
D1	5.21	-	0.205	-	3		Ø	0°	10°	0°	10°			
Е	6.35	6.73	0.250	0.265	5		Ø1	0°	15°	0°	15°			
E1	4.32	-	0.170	=.	3		Ø2	25°	35°	25°	35°			

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension uncontrolled in L5
- (3) Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- (5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (6) Dimension b1 and c1 applied to base metal only
- (7) Datum A and B to be determined at datum plane H
- (8) Outline conforms to JEDEC outline TO-252AA

Revision: 05-Dec-12 Document Number: 95016



Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite Datasheet of VS-10CWH02FNTR-M3 - DIODE ARRAY GP 200V 10A TO252AA

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



www.vishay.com

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Revision: 13-Jun-16 1 Document Number: 91000